

Characteristics
Kennwerte

		T _j = 25°C	Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis					
V _{CE} = 5 V, I _C = 10 μA	Group A	h _{FE}	–	90	–
	Group B		–	150	–
	Group C		–	270	–
V _{CE} = 5 V, I _C = 2 mA	Group A	h _{FE}	110	180	220
	Group B		200	290	450
	Group C		420	520	800
Collector-Emitter saturation voltage – Kollektor-Sättigungsspannung ¹⁾					
I _C = 10 mA, I _B = 0.5 mA	V _{CEsat}	–	90 mV	250 mV	
I _C = 100 mA, I _B = 5 mA		–	200 mV	600 mV	
Base-Emitter saturation voltage – Basis-Sättigungsspannung ²⁾					
I _C = 10 mA, I _B = 0.5 mA	V _{BEsat}	–	700 mV	–	
I _C = 100 mA, I _B = 5 mA		–	900 mV	–	
Base-Emitter-voltage – Basis-Emitter-Spannung ²⁾					
V _{CE} = 5 V, I _C = 2 mA	V _{BE}	580 mV	660 mV	700 mV	
V _{CE} = 5 V, I _C = 10 mA		–	–	720 mV	
Collector-Base cutoff current – Kollektor-Basis-Reststrom					
V _{CB} = 30 V, (E open)	I _{CBO}	–	–	15 nA	
V _{CE} = 30 V, T _j = 125°C, (E open)		–	–	5 μA	
Emitter-Base cutoff current					
V _{EB} = 5 V, (C open)	I _{EBO}	–	–	100 nA	
Gain-Bandwidth Product – Transitfrequenz					
V _{CE} = 5 V, I _C = 10 mA, f = 100 MHz	f _T	–	300 MHz	–	
Collector-Base Capacitance – Kollektor-Basis-Kapazität					
V _{CB} = 10 V, I _E = i _e = 0, f = 1 MHz	C _{CBO}	–	3.5 pF	6 pF	
Emitter-Base Capacitance – Emitter-Basis-Kapazität					
V _{EB} = 0.5 V, I _C = i _c = 0, f = 1 MHz	C _{EBO}	–	9 pF	–	
Thermal resistance junction to ambient Wärmewiderstand Sperrschicht – Umgebung		R _{thA}	< 420 K/W ²⁾		

Disclaimer: See data book page 2 or [website](#)
Haftungsschluss: Siehe Datenbuch Seite 2 oder [Internet](#)

- 1 Tested with pulses $t_p = 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
Gemessen mit Impulsen $t_p = 300\text{ }\mu\text{s}$, Schaltverhältnis $\leq 2\%$
- 2 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss